

**Applications**

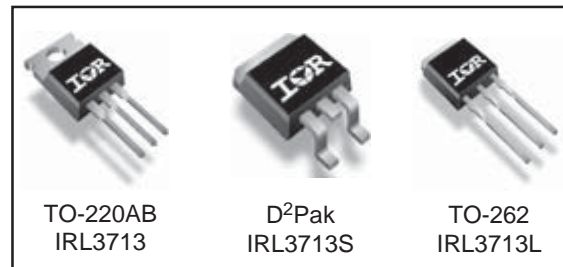
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power
- 100% R<sub>G</sub> Tested

HEXFET® Power MOSFET

V <sub>DS</sub>	R <sub>DS(on)</sub> max (mΩ)	I <sub>D</sub>
30V	3.0@V <sub>GS</sub> = 10V	260A <sup>Ⓞ</sup>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low R<sub>DS(on)</sub> at 4.5V V<sub>GS</sub>
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	260 <sup>Ⓞ</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	180 <sup>Ⓞ</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	1040 <sup>Ⓞ</sup>	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	330	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation	170	
	Linear Derating Factor	2.2	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to +175	°C

**Thermal Resistance**

Symbol	Parameter	Typ	Max	Units
R <sub>θJC</sub>	Junction-to-Case <sup>②</sup>	—	0.45	°C/W
R <sub>qCS</sub>	Case-to-Sink, Flat, Greased Surface <sup>④</sup>	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient <sup>④⑦</sup>	—	62	
R <sub>θJA</sub>	Junction-to-Ambient (PCB Mount) <sup>⑤⑦</sup>	—	40	

Notes <sup>①</sup> through <sup>⑦</sup> are on page 11

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### Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.027	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	2.6	3.0	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 38A ③
		—	3.3	4.0		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 30A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	50	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
		—	—	20		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	100		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -20V

### Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	76	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 30A
Q <sub>g</sub>	Total Gate Charge	—	75	110	nC	I <sub>D</sub> = 30A
Q <sub>gs</sub>	Gate-to-Source Charge	—	24	—		V <sub>DS</sub> = 15V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	37	—		V <sub>GS</sub> = 4.5V ④
Q <sub>oss</sub>	Output Gate Charge	—	61	92		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V
R <sub>G</sub>	Gate Resistance	0.5	—	3.4	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	16	—	ns	V <sub>DD</sub> = 15V
t <sub>r</sub>	Rise Time	—	160	—		I <sub>D</sub> = 30A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	40	—		R <sub>G</sub> = 1.8Ω
t <sub>f</sub>	Fall Time	—	57	—		V <sub>GS</sub> = 4.5V ④
C <sub>iss</sub>	Input Capacitance	—	5890	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	3130	—		V <sub>DS</sub> = 15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	630	—		f = 1.0MHz

### Avalanche Characteristics

Symbol	Parameter	Typ	Max	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	1530	mJ
I <sub>AR</sub>	Avalanche Current ①	—	46	A

### Diode Characteristics

Symbol	Parameter	Min	Typ	Max	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	260 ⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①⑥	—	—	1040 ⑥		
V <sub>SD</sub>	Diode Forward Voltage	—	0.80	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 30A, V <sub>GS</sub> = 0V ③
		—	0.68	—		T <sub>J</sub> = 125°C, I <sub>S</sub> = 30A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	75	110	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 30A, V <sub>R</sub> = 0V
Q <sub>rr</sub>	Reverse Recovery Charge	—	140	210	nC	di/dt = 100A/μs ③
t <sub>rr</sub>	Reverse Recovery Time	—	78	120	ns	T <sub>J</sub> = 125°C, I <sub>F</sub> = 30A, V <sub>R</sub> = 20V
Q <sub>rr</sub>	Reverse Recovery Charge	—	160	240	nC	di/dt = 100A/μs ③

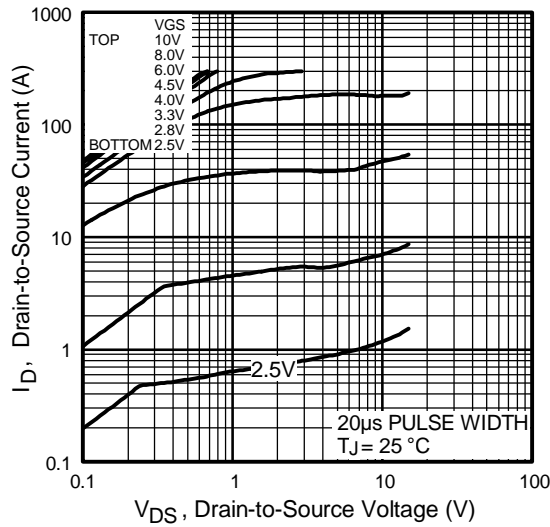


Fig 1. Typical Output Characteristics

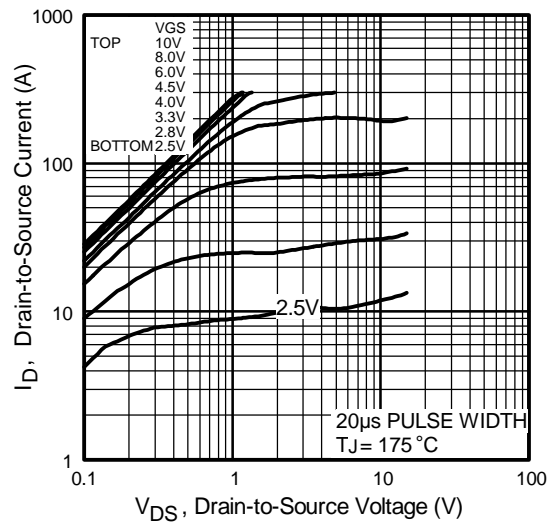


Fig 2. Typical Output Characteristics

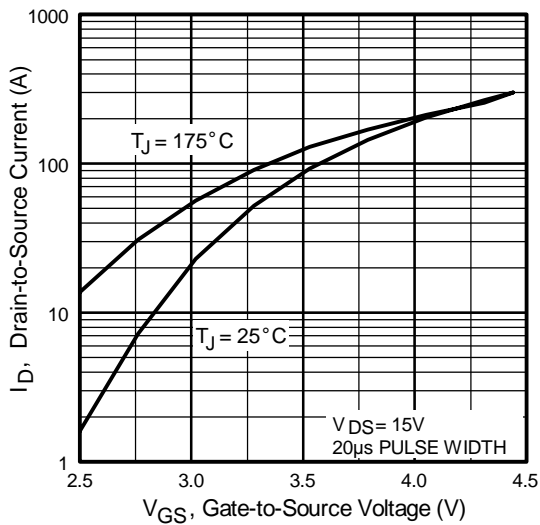


Fig 3. Typical Transfer Characteristics

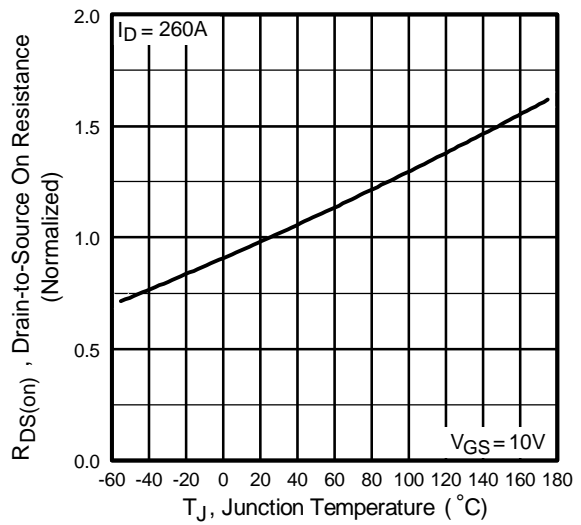


Fig 4. Normalized On-Resistance Vs. Temperature

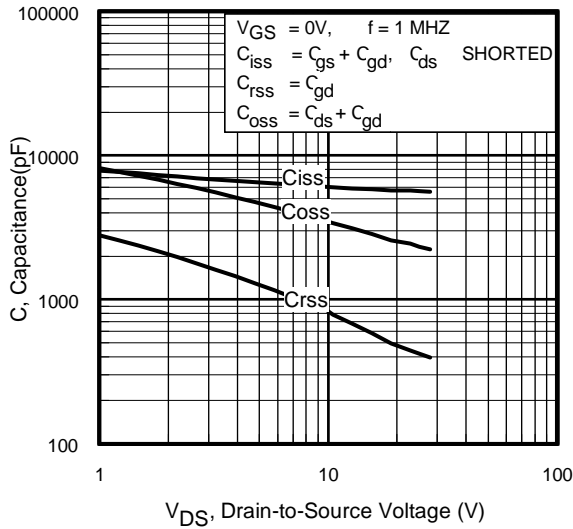


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

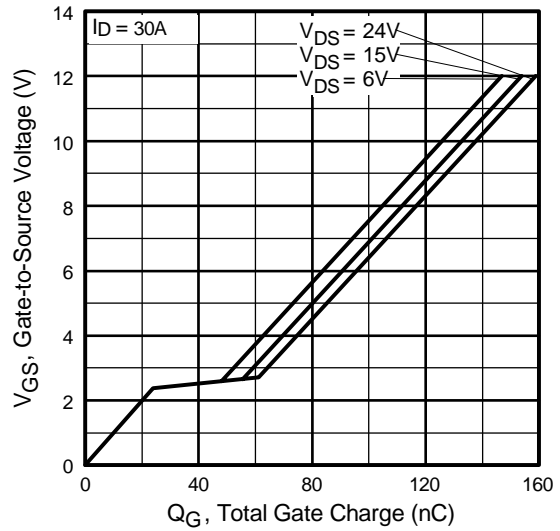


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

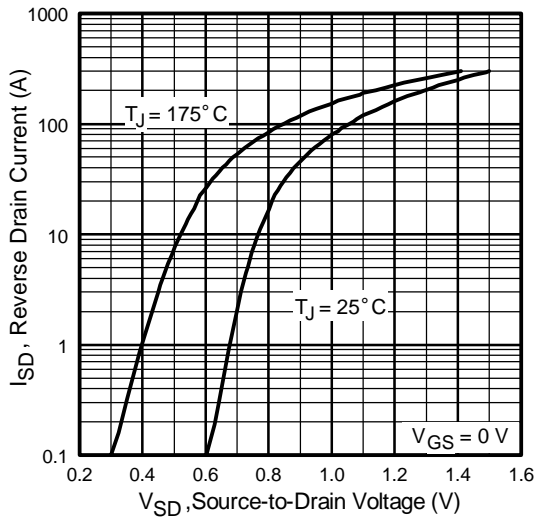


Fig 7. Typical Source-Drain Diode Forward Voltage

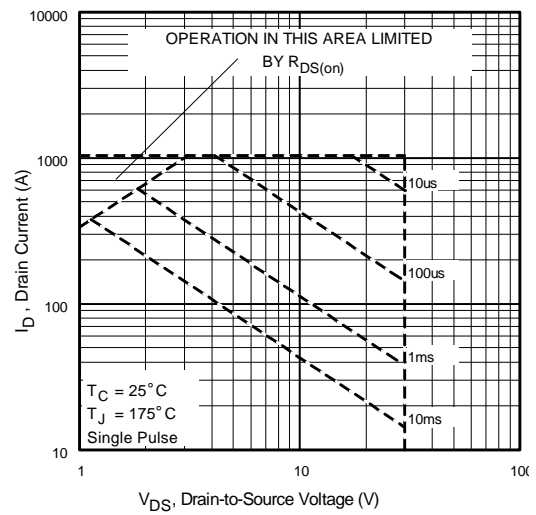


Fig 8. Maximum Safe Operating Area

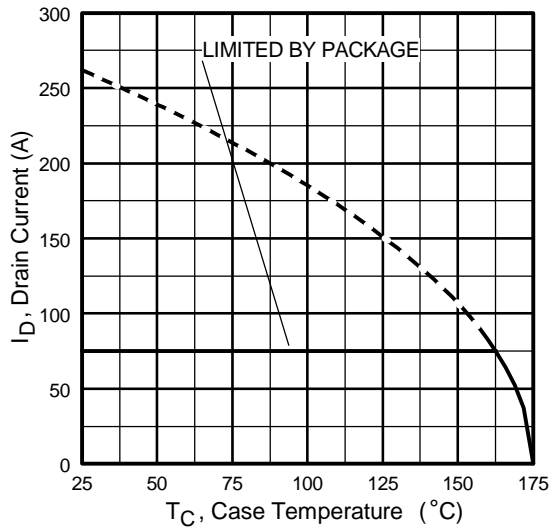


Fig 9. Maximum Drain Current Vs. Case Temperature



Fig 10a. Switching Time Test Circuit

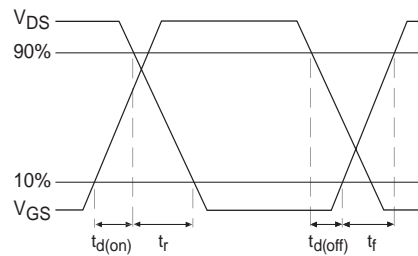


Fig 10b. Switching Time Waveforms

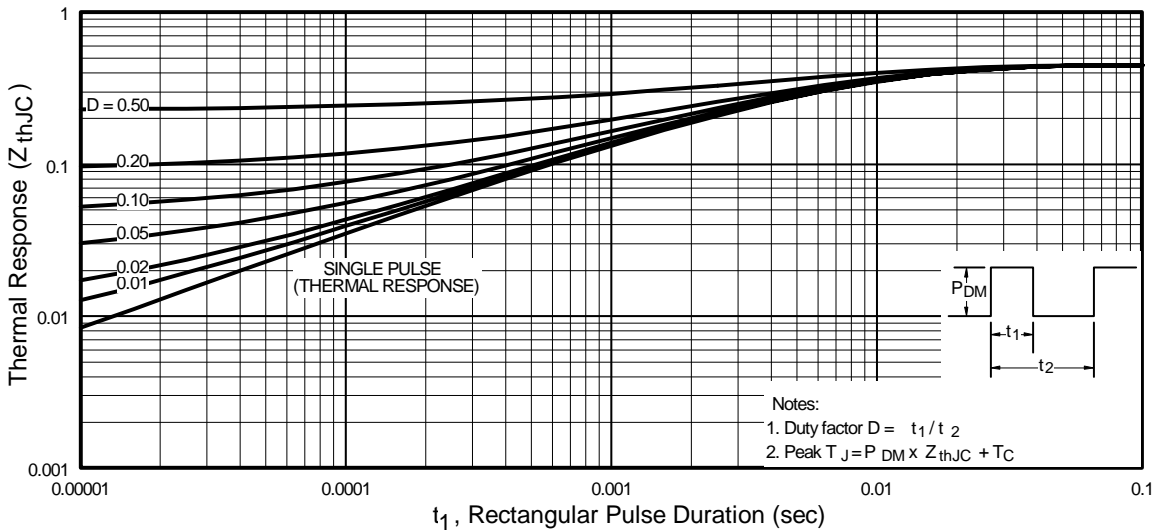


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

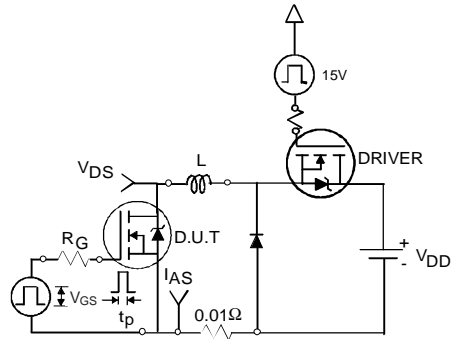


Fig 12a. Unclamped Inductive Test Circuit

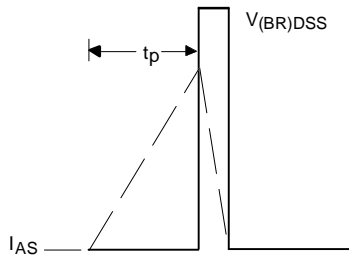


Fig 12b. Unclamped Inductive Waveforms

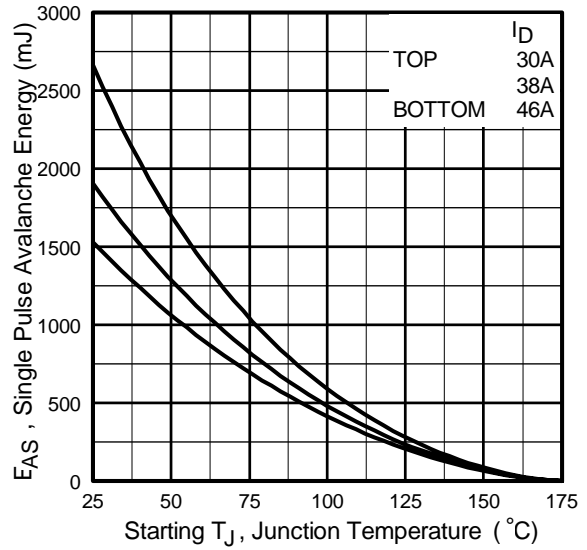


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

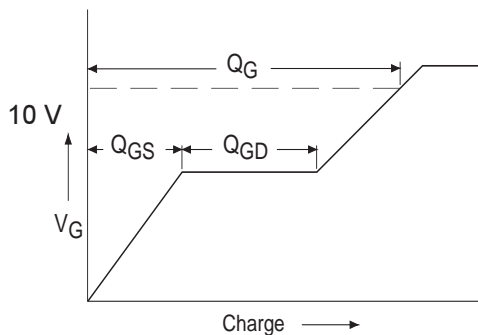


Fig 13a. Basic Gate Charge Waveform

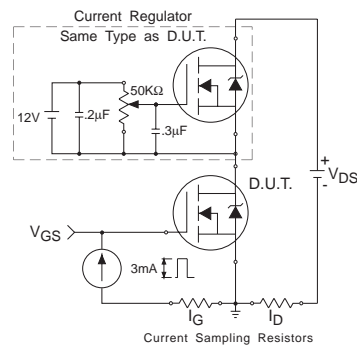
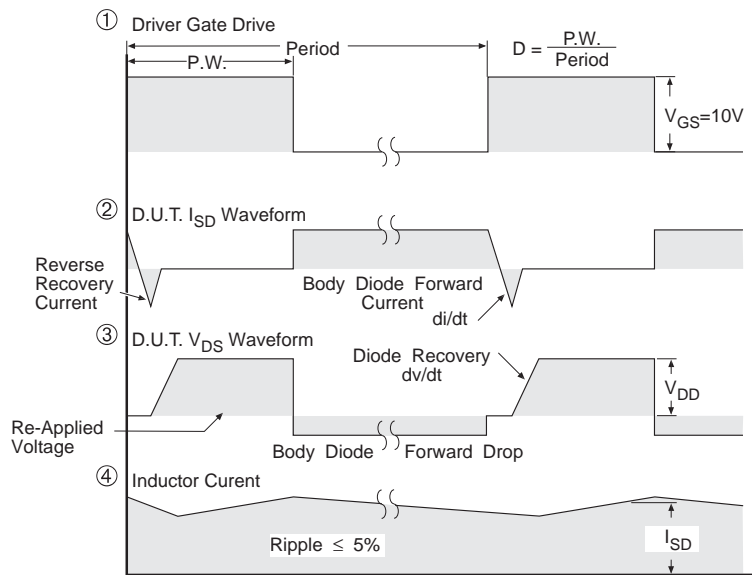
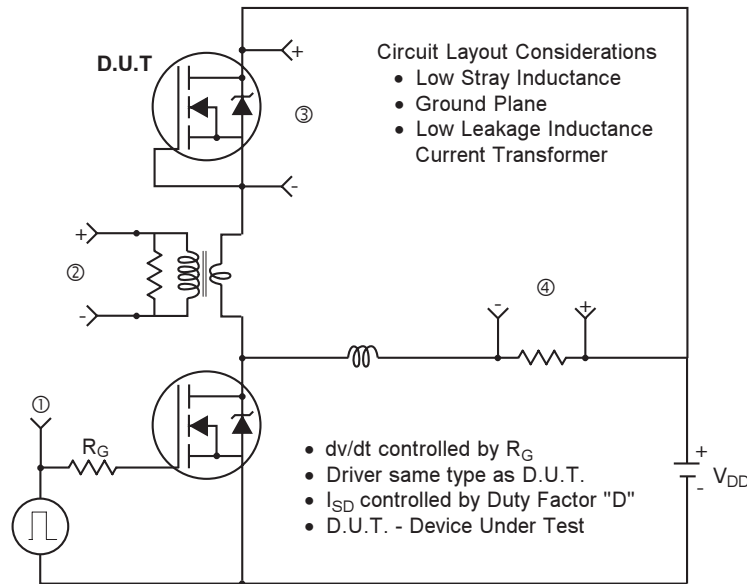


Fig 13b. Gate Charge Test Circuit

### Peak Diode Recovery dv/dt Test Circuit



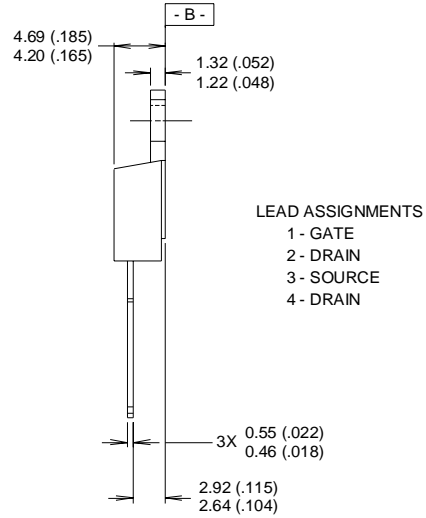
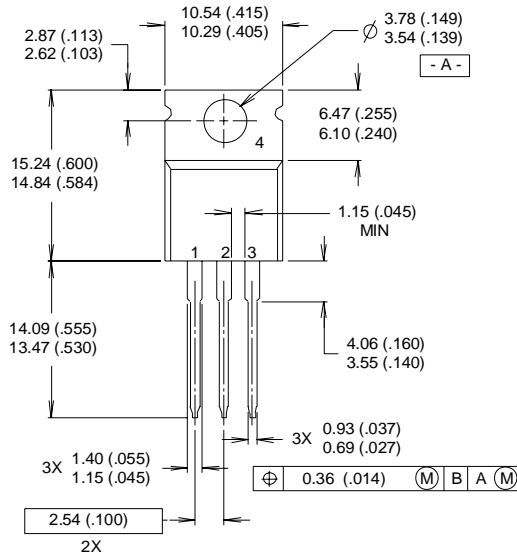
\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRL3713/S/L

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

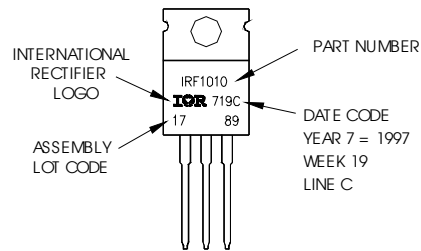


**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

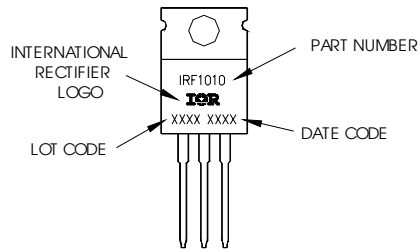
## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"



**For GB Production**

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"

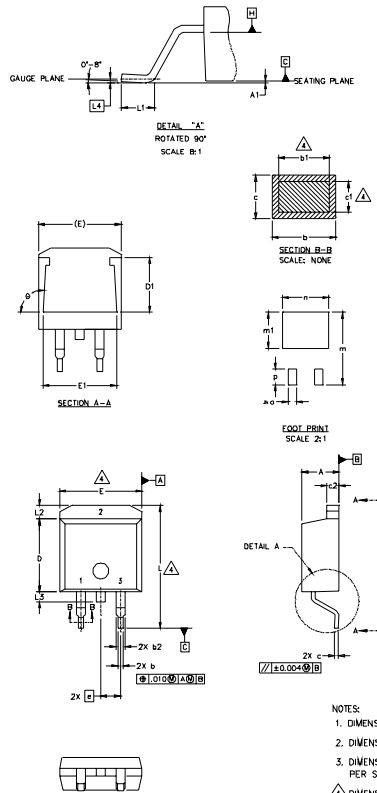




International  
**IR** Rectifier  
**D<sup>2</sup>Pak Package Outline**

IRL3713/S/L

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
theta	90°	9.3°	90°	9.3°	

LEAD ASSIGNMENTS

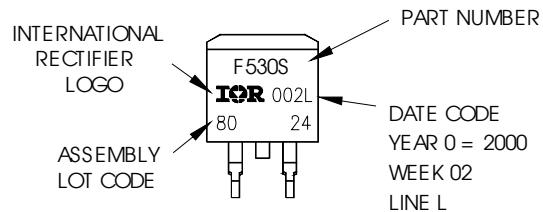
HEFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

\* PART DEPENDENT.

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

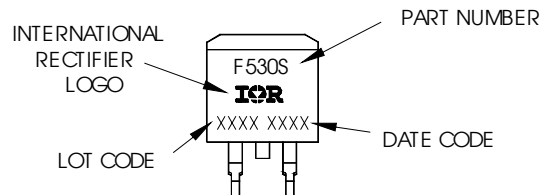
**D<sup>2</sup>Pak Part Marking Information**

EXAMPLE: THIS IS AN IRF530S WITH  
 LOT CODE 8024  
 ASSEMBLED ON WW02, 2000  
 IN THE ASSEMBLY LINE "L"



For GB Production

EXAMPLE: THIS IS AN IRF530S WITH  
 LOT CODE 8024  
 ASSEMBLED ON WW02, 2000  
 IN THE ASSEMBLY LINE "L"

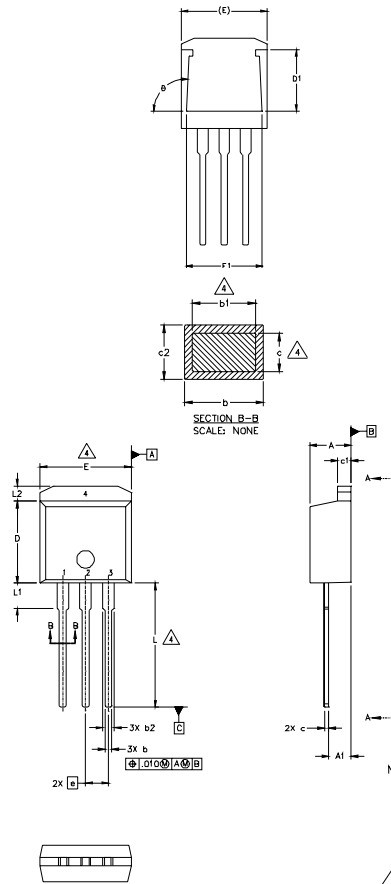


# IRL3713/S/L



## TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

#### IGBT

- 1- GATE
- 2- COLLECTOR

#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"

